

CIR-W3SUSPSA 1808G

DDR3 WIDE TEMP. SO-DIMM 1866MHz 8GB

Description

The CIR-W3SUSPSM1808G is 1024M words X 64 bits, 2 ranks. Unbuffered Small Outline Dual In-Line Memory Module (SO-DIMM). DDR3 SDRAMs in Fine Ball Grid Array (FBGA) packages on a 204pin glass-epoxy substrate. Provide a high performance 8 byte interface in 67.60mm width form factor of industry standard. It is suitable for easy interchange and addition.

Specifications

Density	8GB
Pin Count	204pin
Type	Unbuffered
Dimensions	67.6mm x 30.0mm
ECC	Non-ECC
Component Config	512M x 8 bit
Data Rate	1866 MHz
CAS Latency	13
Voltage	1.5V / 1.35V
PCB Layers	8
Operating Temp.	-40°C~+85°C
Module Ranks	Dual Rank

Features

- Data rate: 1866MHz
- RoHS compliant products.
- 204pin, Small outline dual in-line memory module (SO-DIMM)
- Power supply: VDD= 1.5V (1.425V to 1.575V) & VDD= 1.35V (1.283V to 1.45V)
- Programmable CAS Latency (CL): 6, 7, 8, 9, 10, 11, 12, 13 support
- Fully differential clock inputs (CK, /CK) operation
- Differential Data Strobe (DQS, /DQS)
- Serial presence detect with EEPROM
- 8 independent internal bank
- 8K refresh cycles / 64ms
- On Die Termination supported
- Asynchronous RESET pin supported
- ZQ calibration supported
- Programmable Additive Latency (Posted CAS) : 0, CL - 2, or CL - 1 clock
- Bi-directional Differential Data Strobe
- Burst Length: 4, 8
- 8 bit pre-fetch
- Support Industrial Temp (-40 ~85°C)
- tREFI 7.8us at -40 °C ≤ TCASE ≤ 85°C

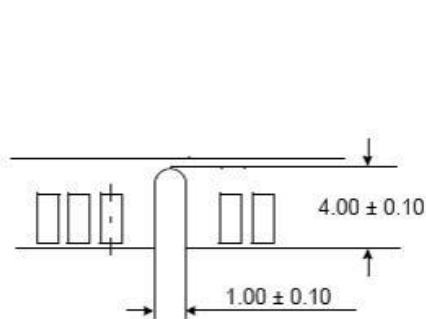
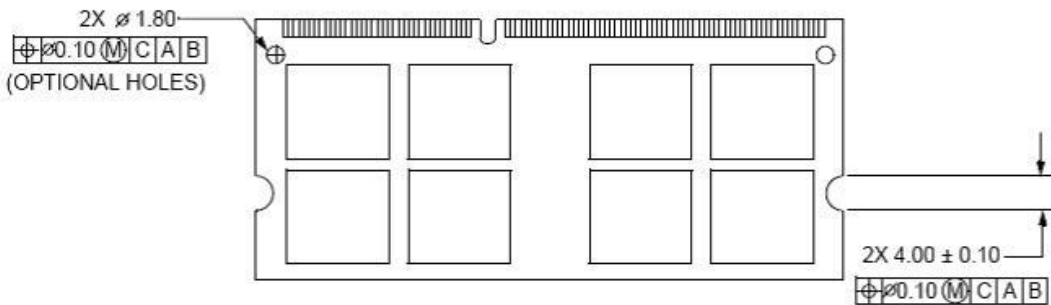
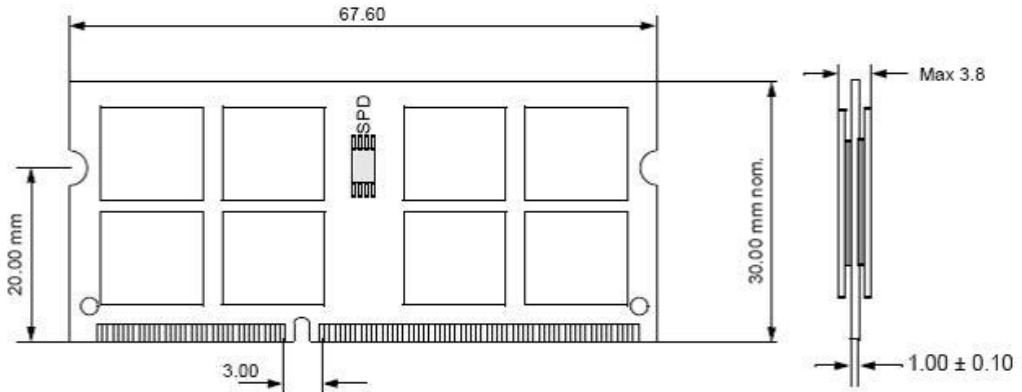


Speed Grade

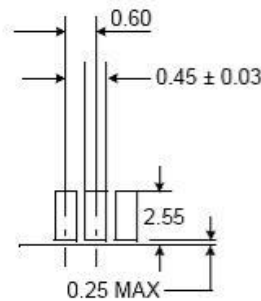
Frequency Grade	Data Transfer Rate	CAS Latency Support								CL-tRCD-tRP
		CL6	CL7	CL8	CL9	CL10	CL11	CL12	CL13	
DDR3-1866	PC3-14900	800	1066	1066	1333	1333	1600	1600	1866	13-13-13

Package Dimensions

Unit: mm



Detail A



Detail B

Tolerances : ± 0.15 mm unless otherwise specified